

**High Voltage Fast-Switching NPN Power Transistor**

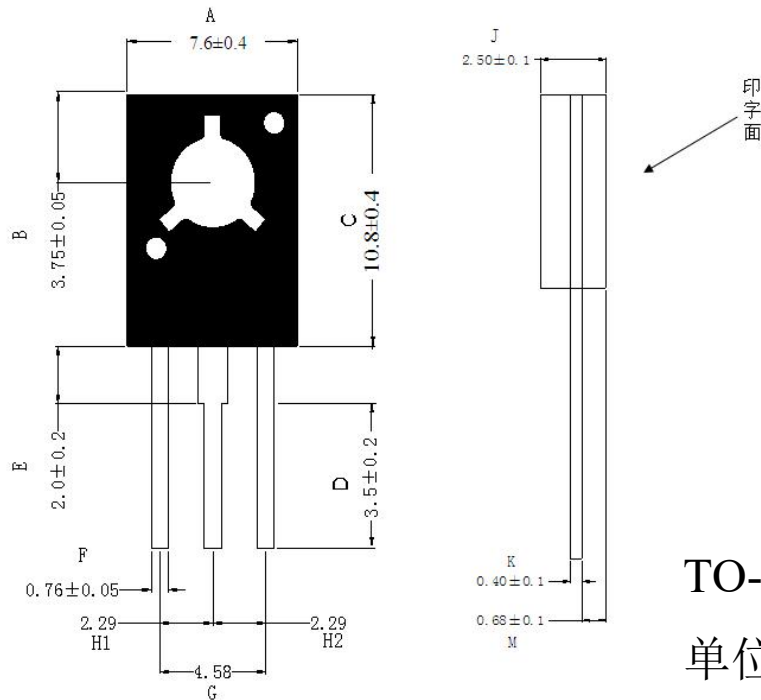
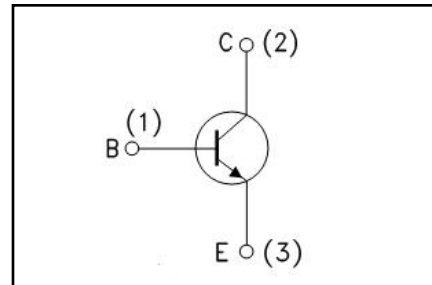
◆ **Features:**

- ◇ High Switching Speed  
开关速度快
- ◇ Low forward voltage drop  
正向压降低
- ◇ High efficiency and low power loss  
高效低功耗
- ◇ High current surge capability  
大电流浪涌能力强



◆ **Applications**

- ◇ Electronic Ballast  
电子镇流器
- ◇ Switching Mode Power Supply  
开关电源
- ◇ Motor Controls  
电机控制
- ◇ Solenoid/Relay drivers and Deflection circuits applications  
电磁阀/继电器驱动器和偏转电路应用



**High Voltage Fast-Switching NPN Power Transistor****◆ Absolute Maximum Ratings (Tc=25°C)**

Symbol	Parameters	Ratings	Unit
VCBO	Collector-Base Voltage 集电极 - 基极电压	<b>700</b>	V
VCEO	Collector-Emitter Voltage 集电极 - 发射极电压	<b>400</b>	V
VEBO	Emitter-Base Voltage 发射极 - 基极电压	<b>9</b>	V
Ic	Collector Current-Continuous 集电极连续电流	<b>2</b>	A
PC	Collector Power Dissipation 耗散功率	<b>30</b>	W
Tj	Max.Operating junction temperature 最大结温	<b>150</b>	°C
Tstg	Storage Temperature 存储温度	<b>-55 ~ +150</b>	°C
Rth(j-c)	Thermal Resistance, Junction to Case 结到外壳的热阻	<b>4.17</b>	°C/W

**High Voltage Fast-Switching NPN Power Transistor**
**◆ Electrical characteristics (Tc=25°C unless otherwise noted)**

Symbol	Parameters	Min	Typ	Max	Units	Conditions
I <sub>CBO</sub>	Collector Cutoff Current 集电极截止电流		--	<b>10</b>	μA	V <sub>CE</sub> =650V, I <sub>B</sub> =0
I <sub>EBO</sub>	Emitter Cutoff Current 发射极截止电流		--	<b>20</b>	μA	V <sub>EB</sub> =9V, I <sub>C</sub> =0
BV <sub>CEO</sub>	Collector Emitter Sustaining voltage(Note 1) 集电极发射极持续电压	<b>400</b>			V	I <sub>C</sub> =10mA, I <sub>B</sub> =0
V <sub>CE(sat)</sub>	Collector Emitter Saturation Voltage(Note 1) 集电极发射极饱和电压			<b>0.6</b>	V	I <sub>C</sub> =1.5A, I <sub>B</sub> =0.3A
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage(Note 1) 基极发射极饱和电压			<b>1.2</b>	V	I <sub>C</sub> =1.5A, I <sub>B</sub> =0.3A
h <sub>FE</sub>	DC Current Gain(Note 1) 直流电流增益	<b>15</b>	--	<b>35</b>		I <sub>C</sub> =0.1A, V <sub>CE</sub> =5V
f <sub>T</sub>	Current-Gain—Bandwidth 电流增益带宽	<b>5</b>	--	--	MHz	V <sub>CE</sub> =10V, I <sub>C</sub> =0.5A, f=1MHz
T <sub>s</sub>	Period of storage 贮存时间	<b>2</b>	--	<b>8</b>	us	I <sub>C</sub> =250mA, UI9600
T <sub>r</sub>	Up time 上升时间	--	--	<b>1</b>	us	
T <sub>f</sub>	Drop-out time 下降时间	--	--	<b>1</b>	us	

Note 1: Pulse test: PW ≤ 300us , duty cycle ≤ 2%.

## X-ON Electronics

Largest Supplier of Electrical and Electronic Components

*Click to view similar products for [Bipolar Transistors - BJT category](#):*

*Click to view products by [OSEN manufacturer](#):*

Other Similar products are found below :

[BC559C](#) [MCH4017-TL-H](#) [MMBT-2369-TR](#) [BC546/116](#) [NJVMJD148T4G](#) [NTE16](#) [NTE195A](#) [IMX9T110](#) [2N4401-A](#) [2N6728](#) [2SA1419T-TD-H](#) [2SB1204S-TL-E](#) [2SC5488A-TL-H](#) [FMC5AT148](#) [2N2369ADCSM](#) [2N2907A](#) [2N3904-NS](#) [2N5769](#) [2SC4618TLN](#) [CPH6501-TL-E](#) [BC856BW-13-F](#) [US6T6TR](#) [BAX18/A52R](#) [BC556/112](#) [IMZ2AT108](#) [MMST8098T146](#) [MCH6102-TL-E](#) [BC846B-13-F](#) [2N3879](#) [30A02MH-TL-E](#) [NTE13](#) [NTE282](#) [NTE323](#) [NTE350](#) [NTE81](#) [JANTX2N2920L](#) [JANSR2N2907AUB](#) [CMLT3946EG TR](#) [SNSS40600CF8T1G](#) [CMLT3906EG TR](#) [GRP-DATA-JANS2N2907AUB](#) [GRP-DATA-JANS2N2222AUA](#) [MMDT3946FL3-7](#) [2N4240](#) [JANS2N3019](#) [MSB30KH-13](#) [2N2221AUB](#) [2SD1815T-TL-E](#) [2N6678](#) [2N2907Ae4](#)